

Usually silicon is considered as the material of choice for systems operating in the Middle Infrared (MIR) region, 3 to 5 μm . But in fact the material may be used in much broader operating range from 1.2 μm to 1000 μm or even more.

Three grades of optical materials are produced to optimize transmission in the operation wavelength region: Optical Czochralski Silicon (OCz-Si), Float Zone Silicon (FZ-Si), and High Resistivity Float Zone Silicon (HRFZ-Si). The choice of above grades depends on the wavelength range, element thickness and application. We use the crystals of appropriate grade (production method, conductivity type and resistance) to guarantee the best transmittance. Main principles of proper material choice are described and demonstrated below. Just in case we shall note the transmittance doesn't depend on the crystal orientation.

In the Fig.1 transmission spectra in NIR and MIR range are shown. Samples' thickness is 5 mm. One can see that in 3 to 5 μm range practically there is no difference in transmission of materials of all used grades and resistances. It is also seen that all grades have phonon absorption peaks stipulated by lattice absorption in 6.5 to 25 μm range. OCz-Si has additional peaks at 5.8 μm , 9.1 μm and 19.4 μm induced by Oxygen vibration absorption. Due to much less Oxygen concentration ($10E16 \text{ cm}^{-3}$ vs. about $10E18 \text{ cm}^{-3}$ in OCz Si) FZ-Si is free of Oxygen peaks and can be used for more critical applications.

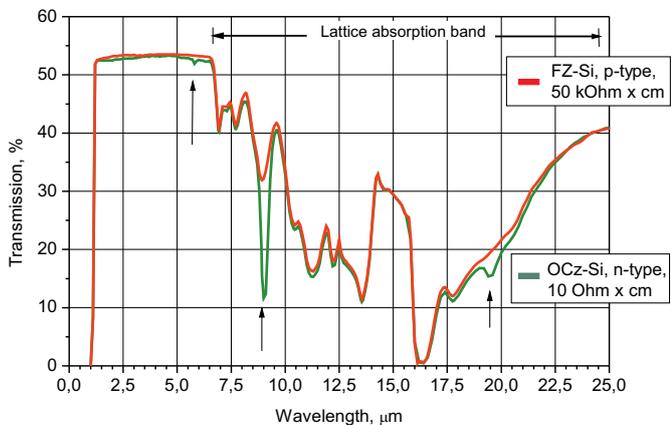


Fig. 1. Silicon transmission in the 1-25 μm spectral range. Arrows point to the oxygen absorption peaks. Sample thickness is 5 mm.

Lattice absorption, as well as Oxygen absorption, depends on the optical pass of radiation inside the element (roughly on element thickness). It does not depend on resistance. Therefore, thickness is a very critical parameter for silicon usage in the range of 6-25 μm .

In Fig. 2 the transmission spectra for several thickness values are shown. One can see that in the 3-5 μm range, typically used in pyrometry and thermography, (and even to 6.5 μm) the transmittance dependence on thickness is not substantial. For longer wavelengths absorption becomes significant and transmission is strongly affected by thickness. For 5-mm thick OCz-Si sample average

transmission over the 8-10 μm band is less than 32% (for FZ-Si about 38%) and only 18% over the 10-14 μm band (the same for both OCz-Si and FZ-Si).

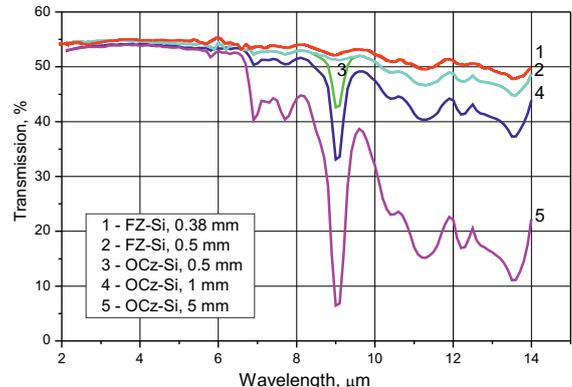


Fig. 2. Transmission of OCz-Si and FZ-Si with respect to thickness.

However silicon windows with thickness less or about 1 mm can also be successfully used in the second "atmosphere window" 7-14 μm . Average transmission of a OCz-Si window with thickness 0.5 mm exceeds 51%, and for FZ-Si it is a bit higher (about 51.9%) due to absence of an Oxygen absorption line.

Transmission in Far Infrared and THz spectral regions is shown in Fig. 3. We note here that starting at 21 μm there is no difference in transmission between FZ-Si and OCz-Si with equal resistance and conductivity type. For such applications (50 μm and more) Tydex offers HRFZ-Si maintaining 50-54% transmission to 1000 μm (and for longer wavelengths on custom request). Materials with the resistance to 30 kOhm x cm are available.

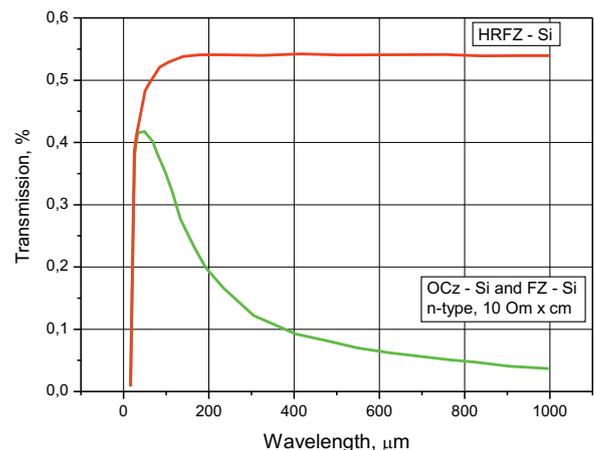


Fig. 3. Silicon transmission. Samples thickness is 5 mm.

Maximal dimensions for crystals used for the optics production are as follows:

- OCz-Si – 300 mm
- FZ-Si – 150 mm
- HRFZ-Si – 150 mm

Physical Properties of Silicon

Density, g/cm ³	2.329
Melting point, °C	1412
Molecular weight	28.09
Surface tension, liquid at mp, mN/m	736
Thermal linear expansion @25°C	2.55 x 10 ⁻⁶
Thermal conductivity @27°C, W/(m x °C)	159
Specific heat capacity (solid), J/(kg x °C)	712
Thermal coefficient of refractive index @ 25°C	1.50 x 10 ⁻⁴
Modulus of rupture, MPa	125
Mohs hardness	7
Young modulus (E), Pa	1.89 x 10 ¹⁰
Shear modulus (G), Pa	7.99 x 10 ¹⁰
Poisson ratio	0.266
Solubility in water	insoluble

Electrical Properties of Silicon

Intrinsic resistivity, kOhm x cm	240	
Intrinsic electron drift mobility, cm ² /(V x s)	1500	
Number of intrinsic electrons, cm ⁻³	1.22 x 10 ¹⁰	
1 Ohm x cm (n-type), 10 ¹⁵ /cm ³	2.93	
1 Ohm x cm (p-type), 10 ¹⁵ /cm ³	7.33	
Intrinsic hole drift mobility, cm ² /(V x s)	600	
Band gap, minimum, eV	300 K	1.14
	0 K	1.17

Silicon Refractive Index vs Wavelength

λ μm	n	λ μm	n
1.40	3.4900	5.83	3.4241
1.50	3.4841	5.92	3.4239
1.66	3.4700	6.00	3.4238
1.82	3.4600	6.50	3.4232
2.00	3.4561	6.92	3.4228
2.50	3.4431	7.00	3.4227
3.00	3.4360	7.14	3.4226
3.30	3.4326	7.30	3.4225
3.50	3.4317	7.50	3.4224
4.00	3.4289	7.72	3.4222
4.50	3.4270	8.00	3.4220
5.00	3.4256	8.16	3.4220
5.19	3.4200	8.50	3.4218
5.50	3.4246	9.00	3.4216
5.70	3.4243	9.09	3.4215

According to the formula

$$n = \sqrt{\epsilon_0},$$

where $\epsilon_0 = 11.67$ is static permittivity, refractive index of silicon tends to 3.416, when wavelength tends to infinity (to 1000 μm and more in our case).



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